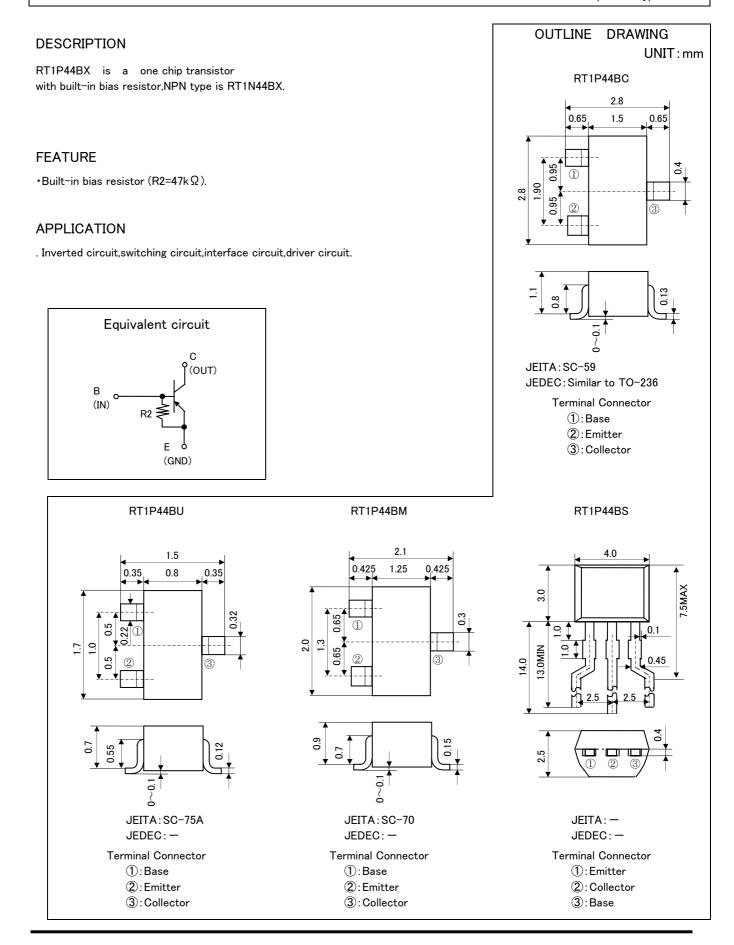
# **RT1P44BX SERIES**

(Transistor)

Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type



ISAHAYA ELECTRONICS CORPORATION

# RT1P44BX SERIES

〈Transistor〉 Transistor With Resistor

For Switching Application Silicon PNP Epitaxial Type

## MARKING

| RT1P44BC<br>RT1P44BM<br>RT1P44BU | RT1P44BS          |
|----------------------------------|-------------------|
| P W<br>type name                 | type name Lot No. |

## MAXIMUM RATING (Ta=25°C)

| SYMBOL           | PARAMETER                      | RATING   |          |          |          |      |
|------------------|--------------------------------|----------|----------|----------|----------|------|
|                  |                                | RT1P44BU | RT1P44BM | RT1P44BC | RT1P44BS | UNIT |
| V <sub>CBO</sub> | Collector to Base voltage      | -50      |          |          |          | V    |
| V <sub>EBO</sub> | Emitter to Base voltage        | -6       |          |          |          | V    |
| V <sub>CEO</sub> | Collector to Emitter voltage   | -50      |          |          |          | V    |
| Ι <sub>c</sub>   | Collector current              | -100     |          |          |          | mA   |
| I <sub>CM</sub>  | Peak Collector current         | -200     |          |          | mA       |      |
| Pc               | Collector dissipation(Ta=25°C) | 150      | 20       | 00       | 450      | mW   |
| Tj               | Junction temperature           | +150     |          |          |          | °C   |
| Tstg             | Storage temperature            | -55~+150 |          |          |          | °C   |

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

| SYMBOL PARAMETER     |                           | LIMIT   |     |      | UNIT |      |
|----------------------|---------------------------|---|-----|------|------|------|
|                      | PARAMETER                 | TEST CONDITION                                |     | TYP  | MAX  | UNIT |
| $V_{(BR)CEO}$        | C to E break down voltage | $I_{c} = -100 \mu A, R_{BE} = \infty$         | -50 | —    | 1    | V    |
| I <sub>CBO</sub>     | Collector cut off current | V <sub>CB</sub> =-50V, I <sub>E</sub> =0      | —   | —    | -0.1 | μA   |
| I <sub>EBO</sub>     | Emitter cut off current   | $V_{EB}$ =-5V, I <sub>c</sub> =0              | -80 | -106 | -154 | μA   |
| h <sub>FE</sub>      | DC forward current gain   | V <sub>CE</sub> =-5V, I <sub>C</sub> =-5mA    | 68  | —    | -    | —    |
| V <sub>CE(sat)</sub> | C to E saturation voltage | I <sub>c</sub> =–10mA, I <sub>B</sub> =–0.5mA | —   | —    | -0.3 | V    |
| R <sub>2</sub>       | Emitter-base resistor     | _   | 33  | 47   | 61   | kΩ   |
| f <sub>T</sub>       | Gain band width product   | V <sub>CE</sub> =-6V, I <sub>E</sub> =10mA    | —   | 150  | _    | MHz  |

# **RT1P44BX SERIES**

Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

DC FORWARD CURRENT GAIN

VS COLLECTOR CURRENT

-10

COLLECTOR CURRENT IC(mA) COLLECTOR CURRENT

VS INPUT OFF VOLTAGE

-1

-0.5

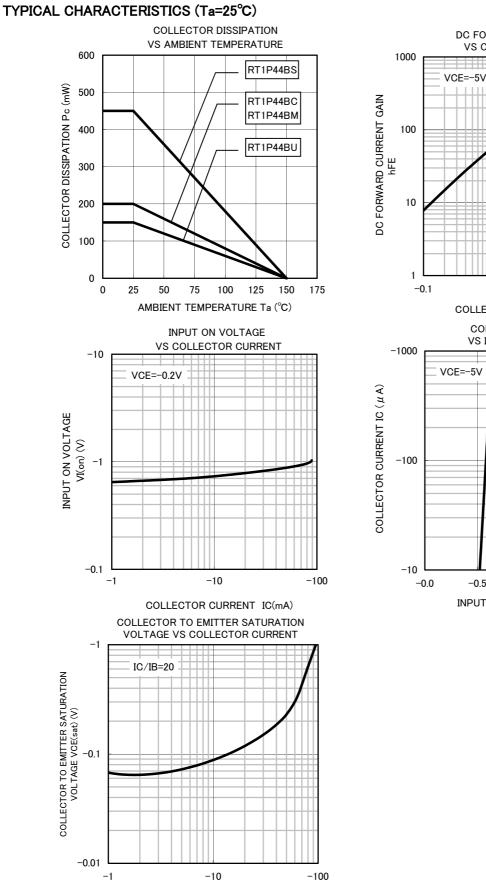
-1.0

INPUT OFF VOLTAGE VI(off) (V)

-1.5

-2.0

-100



COLLECTOR CURRENT IC(mA)

ISAHAYA ELECTRONICS CORPORATION

### (Transistor)

## ISAHAYA ELECTRONICS CORPORATION

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